Icemos Technology Ltd **Product Specification** **1000.683501** Issue Date 31 March 2021 10:02

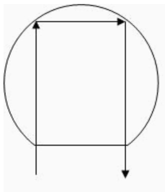
Part Number Customer

Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	200.00 +/- 0.20 mm	Wafer Vendor
	2.0	Notch or Flat	Notch	Wafer Vendor
	3.0	Notch Direction	<110> +/- 0.5 degree	Wafer Vendor
	4.0	Overall Thickness	750.30 +/- 17.00 µm	ADE, 100%
	5.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	6.0	Bow	<70.00µm	ADE 100%, SEMI MF1530
	7.0	Warp	<70.00µm	ADE 100%, SEMI MF1530
	8.0	Edge Chips	none	Bright Light, 100%
	9.0	Edge Exclusion	5mm	
HandleSilicon	10.0	Handle Growth Method	CZ	Wafer Vendor
	11.0	Handle Orientation	{100} +/- 1.0 degree	Wafer Vendor
	12.0	Handle Thickness	600.00 +/- 15.00 µm	ADE, 100%
	13.0	Handle Doping Type	N	Wafer Vendor
	14.0	Handle Dopant	Any	Wafer Vendor
	15.0	Handle Resistivity	>1 Ohm-cm	Wafer Vendor
	16.0	Backside Finish	Polished with oxide and laser mark	Guaranteed by process
BuriedOxide	17.0	Oxide Type	Thermal	
	18.0	Oxide Thickness	3,000.00 +/- 150.00 A	Nanospec centre point, 4%
	19.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	20.0	Device Orientation	{100} +/- 1.0 degree	Wafer Vendor
	21.0	Nominal Thickness	150.00 +/- 1.00 µm	FTIR, 100% 9-Pt (note3)
	22.0	Distance to device silicon edge from wafer edge	<= 2.0mm	Typical by Process
	23.0	Device Doping Type	Any	Wafer Vendor
	24.0	Device Dopant	Any	Wafer Vendor
	25.0	Device Growth Method	Any	Wafer Vendor
	26.0	Device Resistivity	Any	Wafer Vendor
	27.0	Voids	none	Bright Light, 100% (note 2)
	28.0	Scratches	Frontside - no scratches allowed. Backside - light handling marks	Bright Light, 100% (note 2)
	29.0	Haze	none	Bright Light, 100% (note 2)

Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 200.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

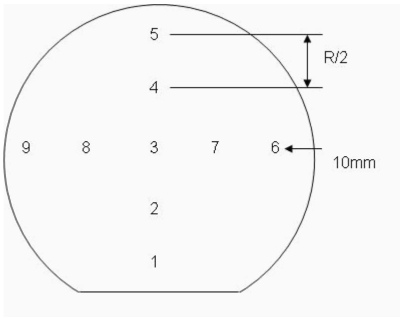
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information